



10-614-368

Co/C

PATENT
Customer No. 22,852
Attorney Docket No. 4329.2340-01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent No.: 6,812,535 B2)
Inventors: ATSUSHI YAGISHITA ET AL.)
Issue Date.: November 2, 2004)
For: SEMICONDUCTOR DEVICE WITH)
A DISPOSABLE GATE AND)
METHOD OF MANUFACTURING)
THE SAME)

Certificate
DEC 03 2004
of Correction

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

REQUEST FOR CERTIFICATE OF CORRECTION

Pursuant to 35 U.S.C. § 254, and 37 C.F.R. § 1.322, this is a request for a Certificate of Correction in the above-identified patent. The mistakes identified in the appended Form occurred through the fault of the Patent Office, as clearly disclosed by the records of the application which matured into this patent.

Two (2) copies of PTO Form 1050 are appended. The complete Certificate of Correction involves one (1) page. Issuance of the Certificate of Correction containing the correction is earnestly requested.

Please charge any required fees not included herewith to our deposit account 06-0916.

Respectfully submitted,

FINNEGAN, HENDERSON, FARABOW,
GARRETT & DUNNER, L.L.P.

Dated: _____

11/30/04

By: _____

Richard V. Burgujian
Reg. No. 31,744

DEC 06 2004

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. 6,812,535 B2
DATED: November 2, 2004
INVENTORS: Yagishita et al.

It is hereby certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page, item (57), in the Abstract, delete in its entirety and insert therefor:

--A semiconductor device with a source and drain formed in a semiconductor substrate; a crystallized gate insulating film formed on the substrate in a region between the source semiconductor and drain; gate electrode formed on the gate insulating and film; an insulating film formed on a side surface of the gate electrode and having an amorphous structure formed from the same material as that of the gate insulating film. Furthermore the insulating film is essentially formed from a material selected from the group consisting of cerium oxide (CeO₂), zirconium oxide (ZrO₂), hafnium oxide (HfO₂), thorium oxide (ThO₂), yttrium oxide (Y₂O₃), calcium fluoride (CaF₂), tin-calcium fluoride (CaSnF₂), titanium-barium oxide (BaTiO₂), and La₂O₃--.

MAILING ADDRESS OF SENDER

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1300 I Street, N.W.
Washington, D.C. 20005-3315

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